



**8NM50**

Preliminary

**Power MOSFET**

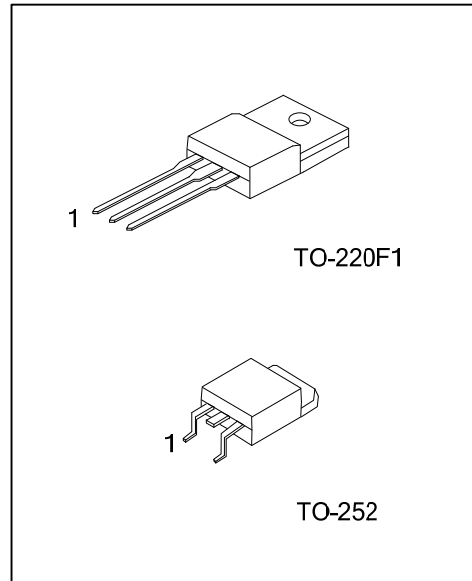
**8.0A, 500V N-CHANNEL SUPER-JUNCTION MOSFET**

■ DESCRIPTION

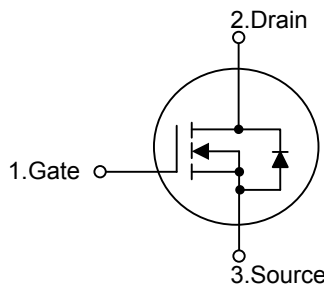
The **UTC 8NM50** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at DC-DC, AC-DC converters for power applications.

■ FEATURES

- \*  $R_{DS(ON)} < 0.49\Omega @ V_{GS}=10V, I_D=4.0A$
- \* High Switching Speed
- \* 100% Avalanche Tested



■ SYMBOL



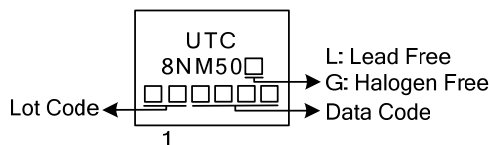
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
8NM50L-TF1-T	8NM50G-TF1-T	TO-220F1	G	D	S	Tube
8NM50L-TN3-R	8NM50G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>8NM50L-TF1-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Green Package</p>	<p>(1) T: Tube, R: Tape Reel</p> <p>(2) TF1: TO-220F1, TN3: TO-252</p> <p>(3) L: Lead Free, G: Halogen Free and Lead Free</p>
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■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ( $T_c=25^\circ\text{C}$ , unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{DSS}$	500	V
Gate-Source Voltage		$V_{GSS}$	$\pm 30$	V
Drain Current	Continuous	$I_D$	8.0	A
	Pulsed (Note 2)	$I_{DM}$	32	A
Avalanche Current (Note 2)		$I_{AR}$	3.3	A
Avalanche Energy	Single Pulsed (Note 3)	$E_{AS}$	54	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	8.0	V/ns
Power Dissipation	TO-220F1	$P_D$	42	W
	TO-252		80	W
Junction Temperature		$T_J$	+150	$^\circ\text{C}$
Storage Temperature		$T_{STG}$	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3.  $L = 10\text{mH}$ ,  $I_{AS} = 3.3\text{A}$ ,  $V_{DD} = 50\text{V}$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$

4.  $I_{SD} \leq 8.0\text{A}$ ,  $di/dt \leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$

■ THERMAL DATA

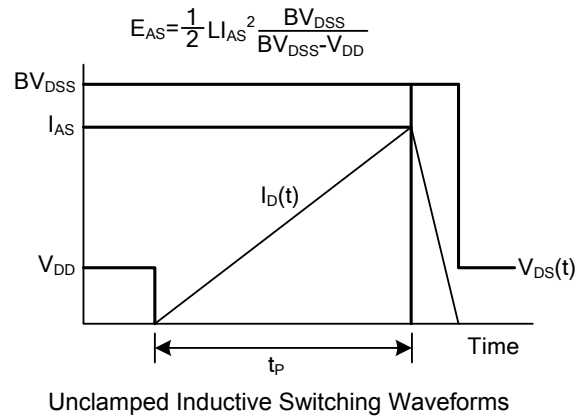
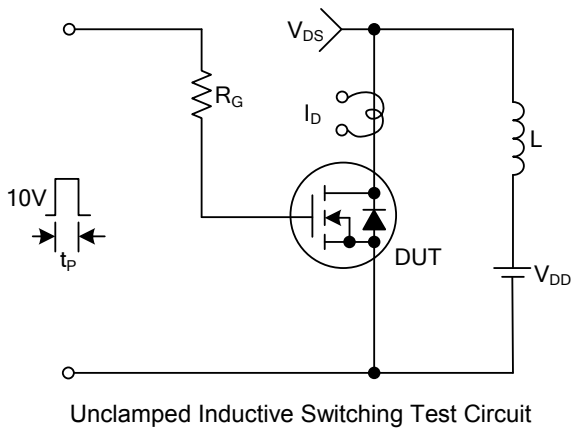
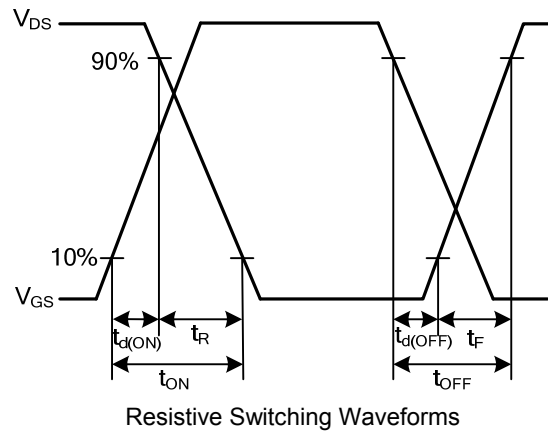
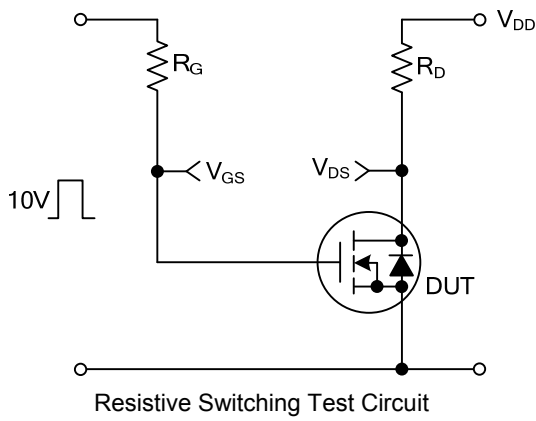
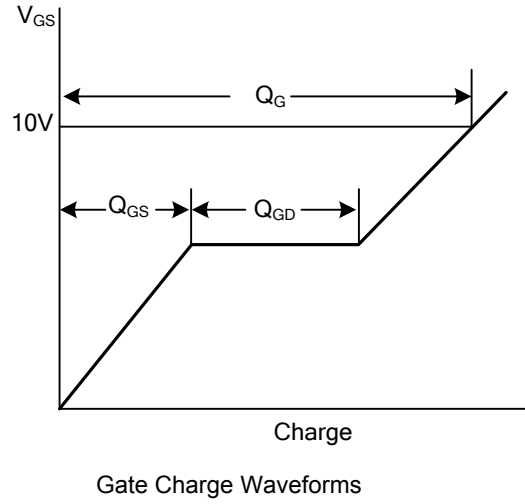
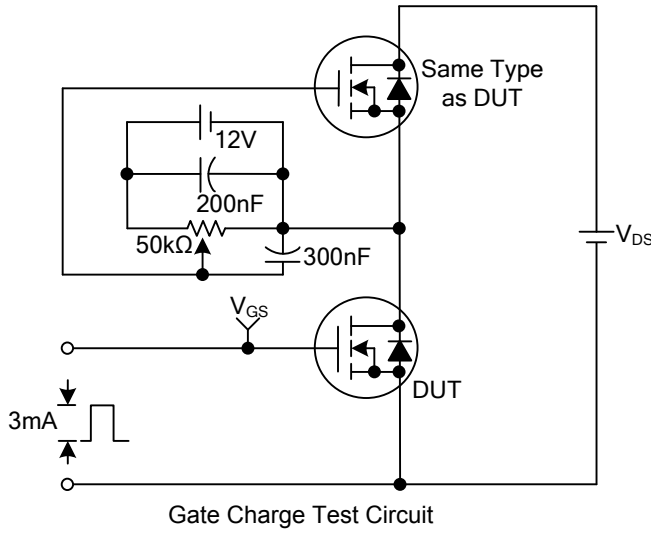
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220F1	$\theta_{JA}$	62.5	$^\circ\text{C}/\text{W}$
	TO-252		110	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220F1	$\theta_{JC}$	3	$^\circ\text{C}/\text{W}$
	TO-252		1.56	$^\circ\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS (T<sub>J</sub> =25°C, unless otherwise noted)

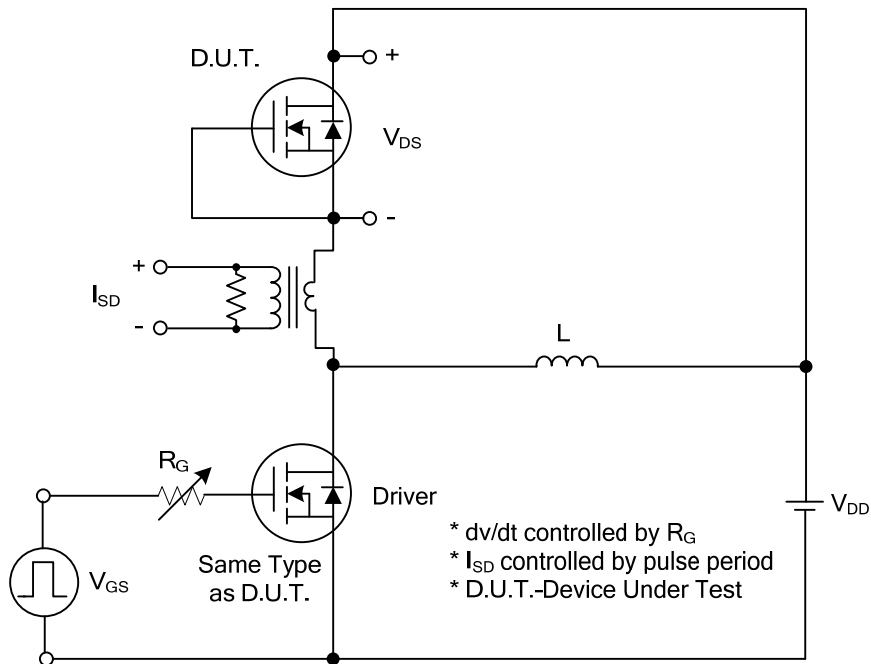
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	500			V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =500V, V <sub>GS</sub> =0V			1	μA
Gate- Source Leakage Current	Forward	I <sub>GSS</sub> V <sub>GS</sub> =+30V, V <sub>DS</sub> =0V			+100	nA
	Reverse		V <sub>GS</sub> =-30V, V <sub>DS</sub> =0V			-100
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	2.5		4.5	V
Static Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =4.0A			0.49	Ω
<b>DYNAMIC PARAMETERS</b>						
Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1.0MHz		460		pF
Output Capacitance	C <sub>OSS</sub>			430		pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			62		pF
<b>SWITCHING PARAMETERS</b>						
Total Gate Charge (Note 1)	Q <sub>G</sub>	V <sub>DS</sub> =50V, I <sub>D</sub> =1.3A, I <sub>G</sub> =100μA V <sub>GS</sub> =10V (Note 1,2)		30		nC
Gate to Source Charge	Q <sub>GS</sub>			3		nC
Gate to Drain Charge	Q <sub>GD</sub>			13		nC
Turn-ON Delay Time (Note 1)	t <sub>D(ON)</sub>	V <sub>DD</sub> =30V, I <sub>D</sub> =0.5A, R <sub>G</sub> =25Ω, V <sub>GS</sub> =10V (Note 1,2)		50		ns
Rise Time	t <sub>R</sub>			104		ns
Turn-OFF Delay Time	t <sub>D(OFF)</sub>			182		ns
Fall-Time	t <sub>F</sub>			93		ns
<b>SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS</b>						
Maximum Body-Diode Continuous Current	I <sub>S</sub>				8.0	A
Maximum Body-Diode Pulsed Current	I <sub>SM</sub>				32	A
Drain-Source Diode Forward Voltage (Note 1)	V <sub>SD</sub>	I <sub>S</sub> =8.0A, V <sub>GS</sub> =0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)	t <sub>rr</sub>	I <sub>S</sub> =8.0A, V <sub>GS</sub> =0V, dI <sub>F</sub> /dt=100A/μs		270		ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>				3.05	

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%  
2. Essentially independent of operating temperature

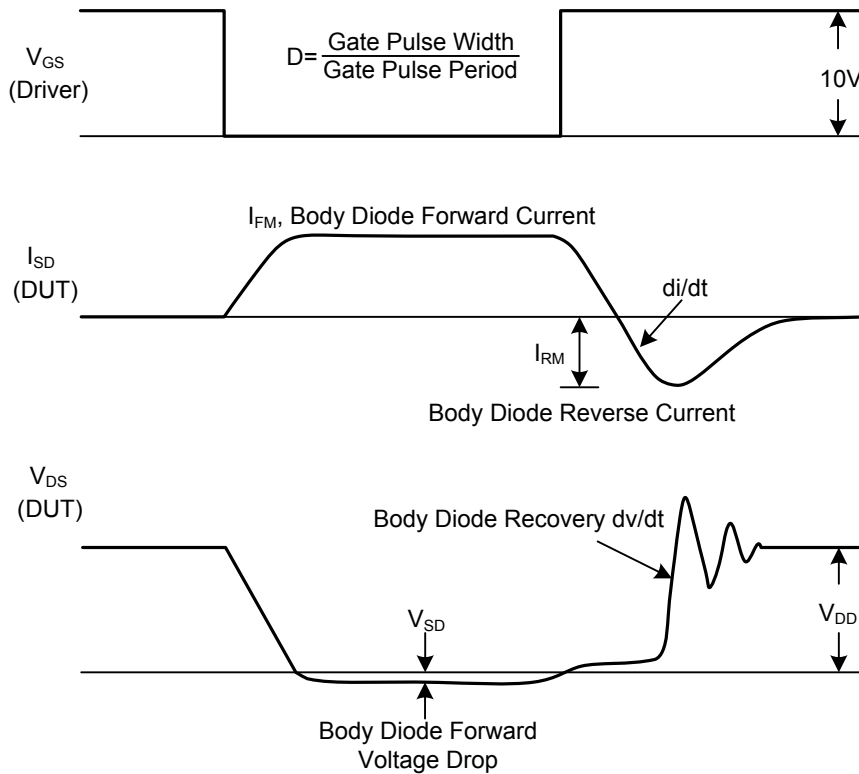
■ TEST CIRCUITS AND WAVEFORMS



■ TEST CIRCUITS AND WAVEFORMS(Cont.)



Peak Diode Recovery dv/dt Test Circuit & Waveforms



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